

Development of Advanced High-Performance Organic Photovoltaic Device

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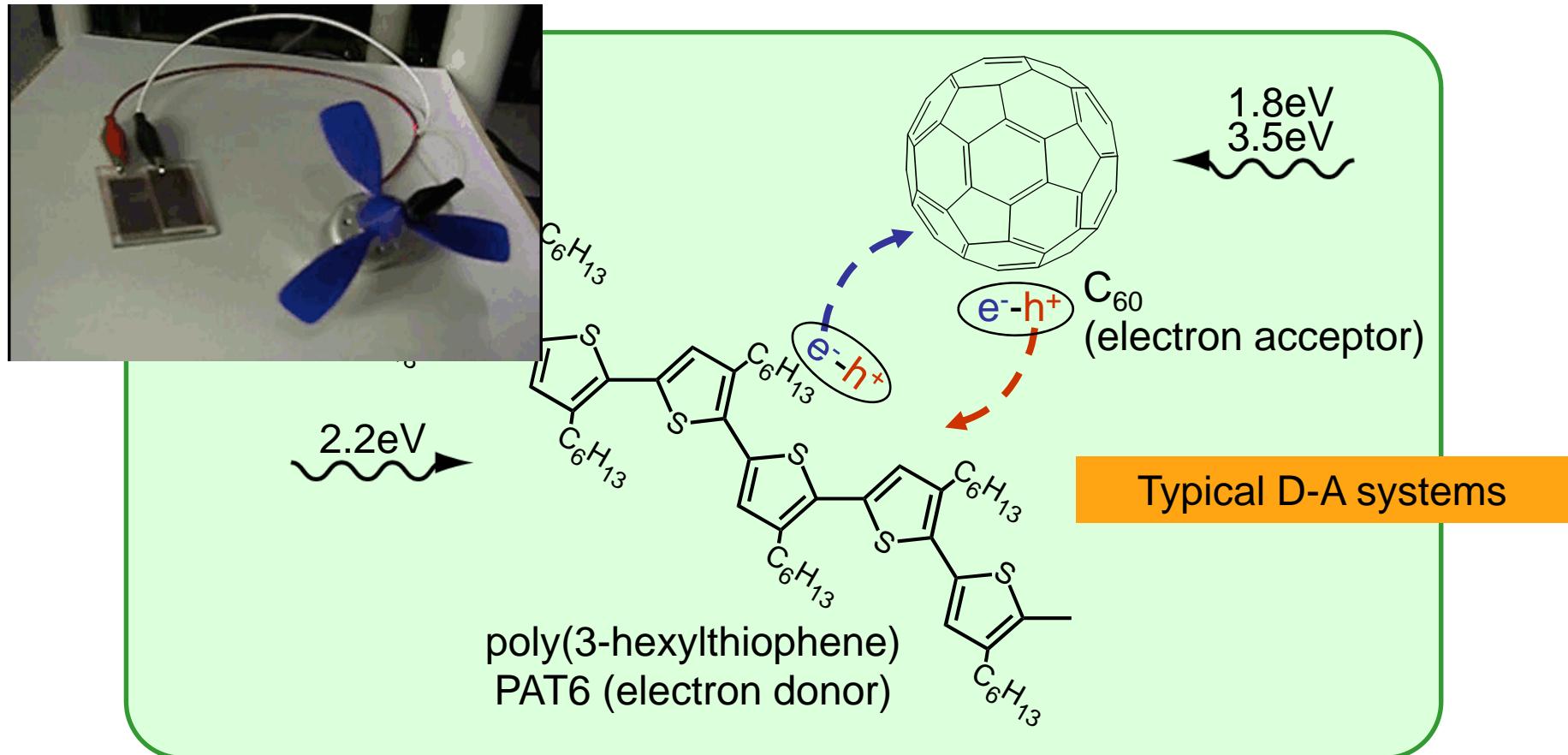
Y. Miyake and Y. Shimizu (Advanced Industrial Science and Technology Kansai, Japan)

EDIS2008 Satellite meeting “Recent Activities of IDER units”

January 18, 2008

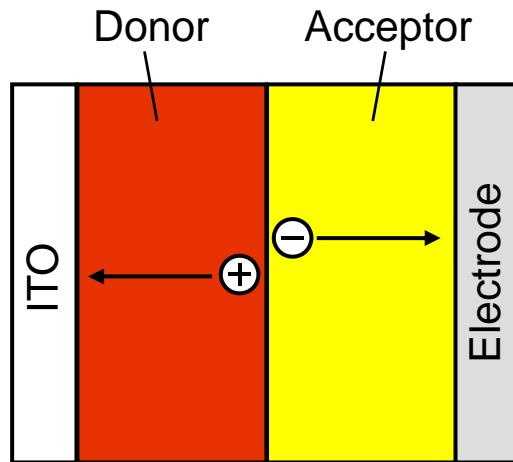
π-Conjugated Polymer-Fullerene Systems

Famous phenomenon, such as photo-induced charge transfer, is fundamental mechanism in polymer photovoltaic devices

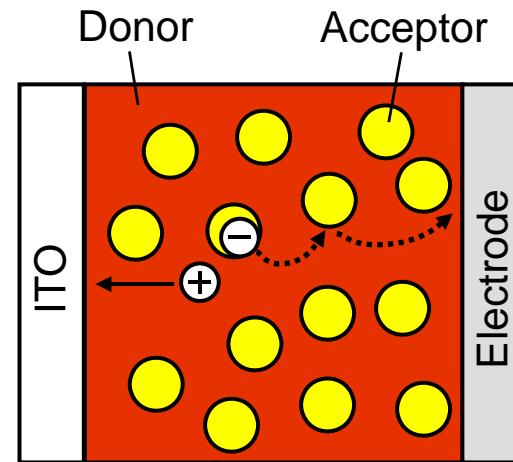


- Ref. [1] S. Morita, et al.: Solid State Commun. **82** (1992) 249.
[2] K. Yoshino, et al.: Solid State Commun. **85** (1993) 85.
[3] N. S. Sariciftci, et al.: Science **270** (1995) 1789.

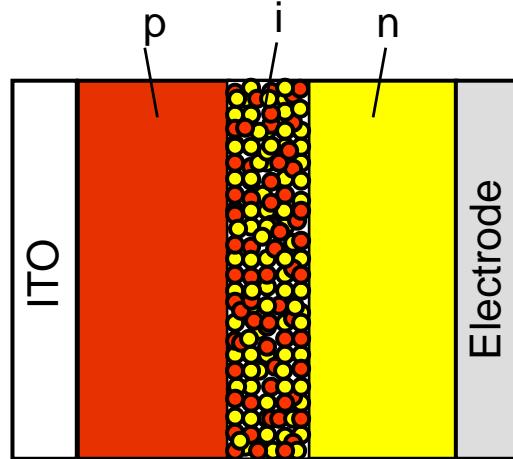
Fundamental Structures of D-A Type Photovoltaic Cells



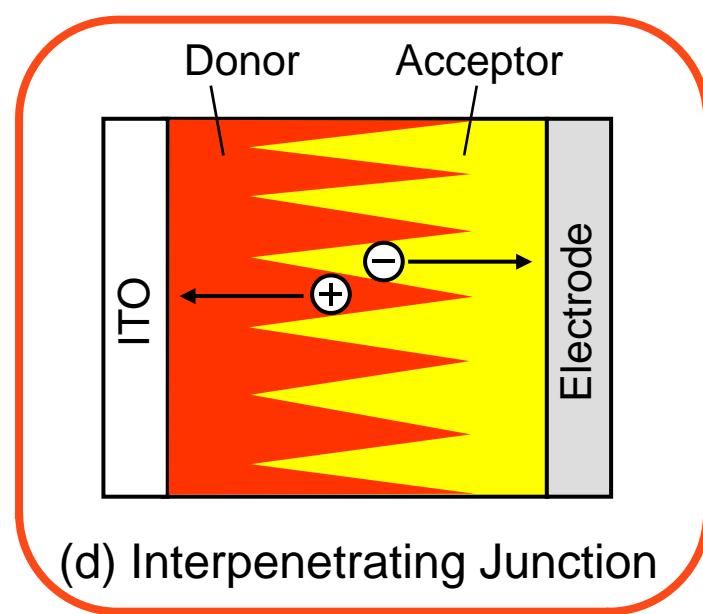
(a) Bi-layer type



(b) Bulk Heterojunction

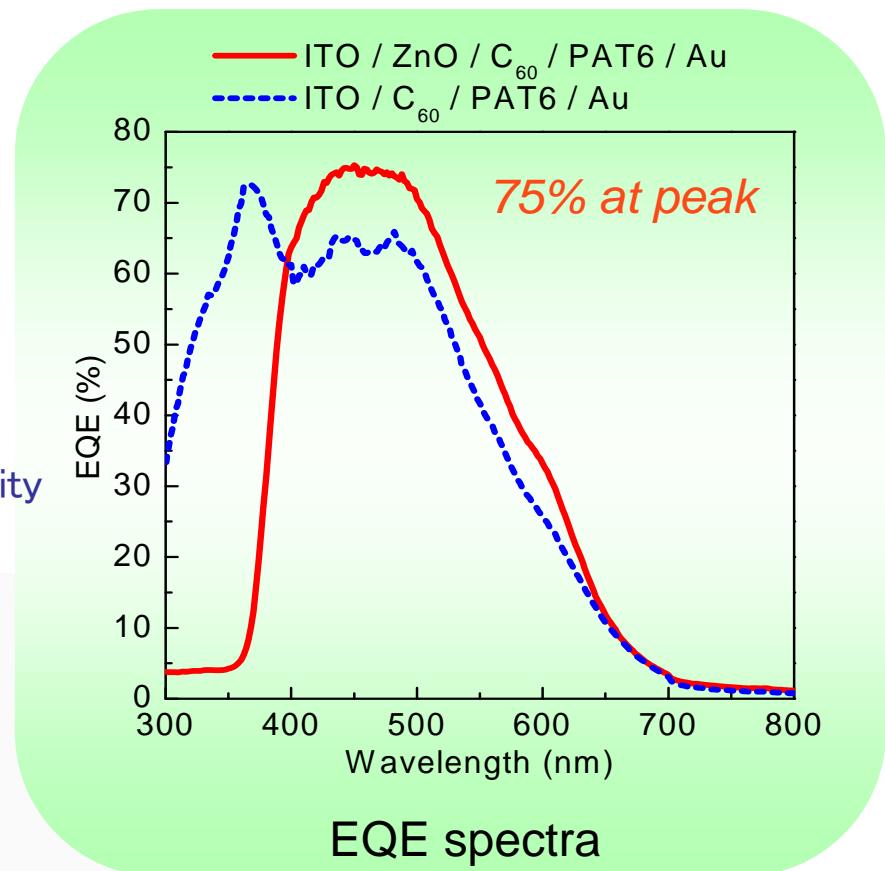
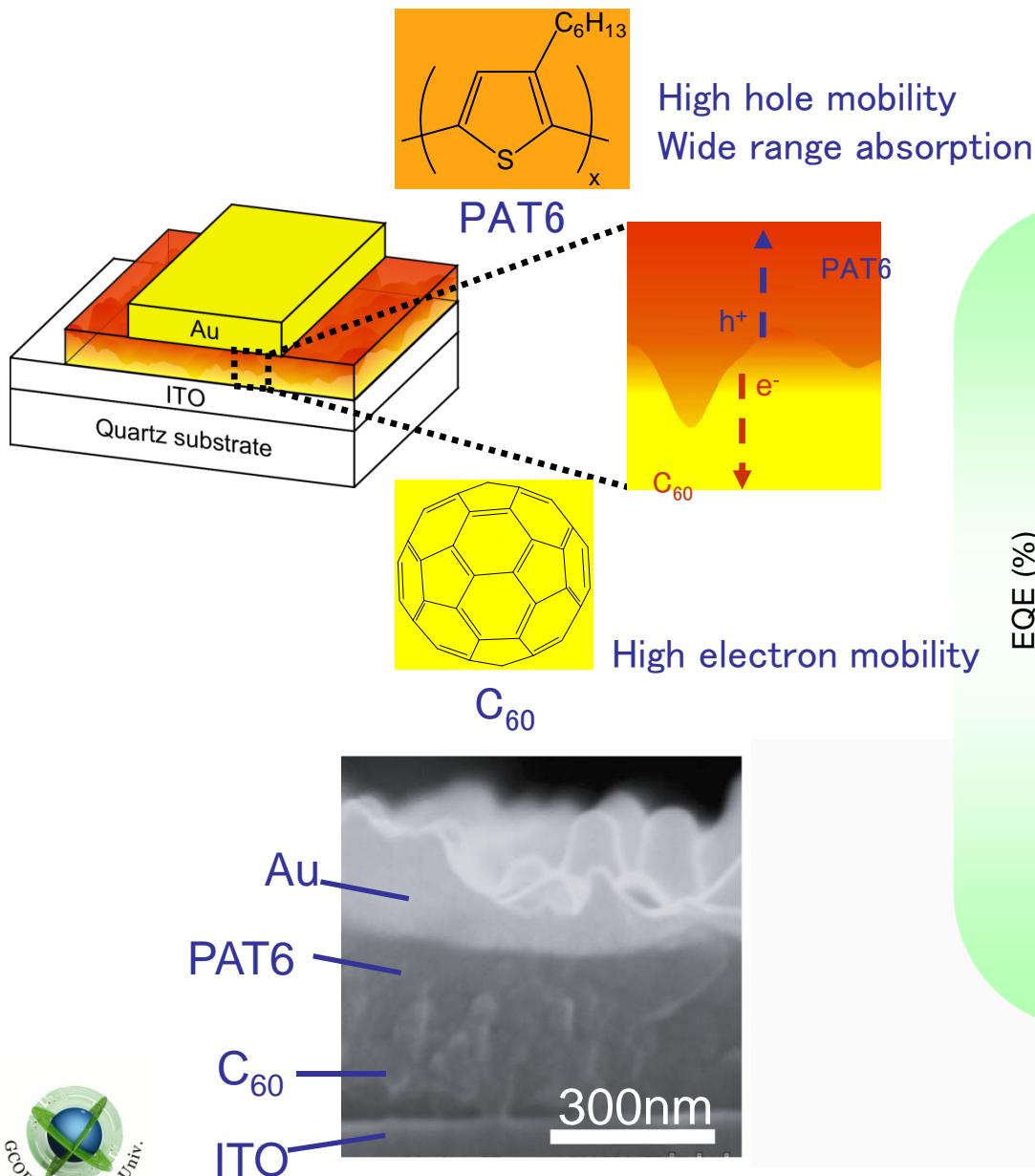


(c) p-i-n Junction Type



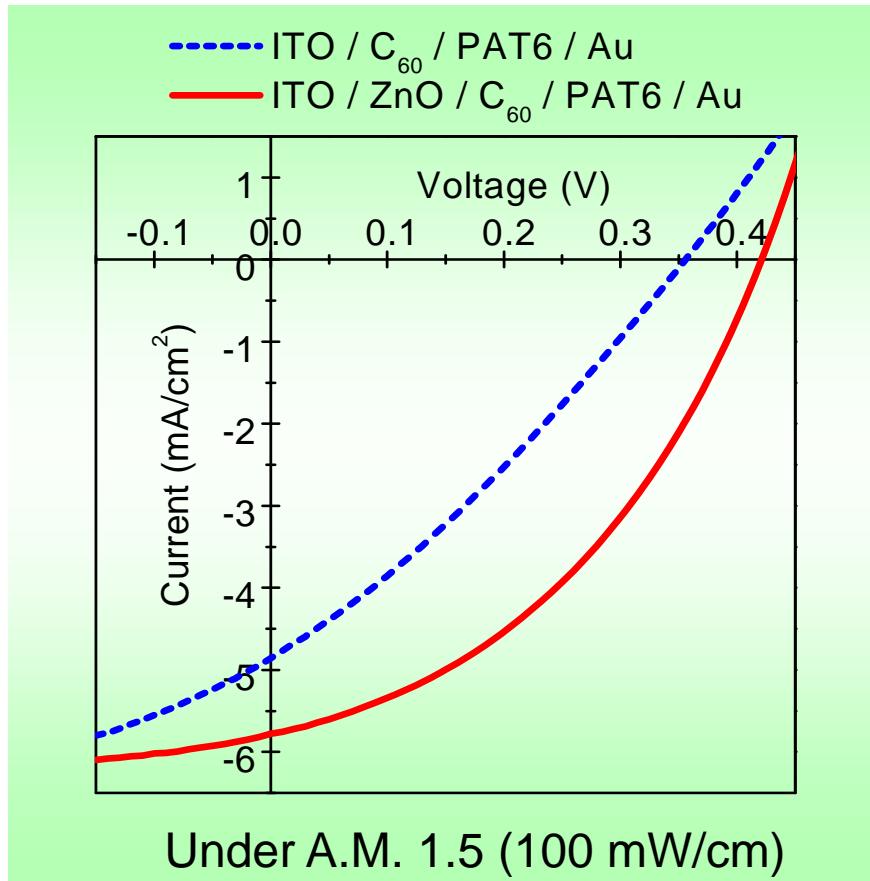
(d) Interpenetrating Junction

Device Performance of Interpenetrating Junction Devices

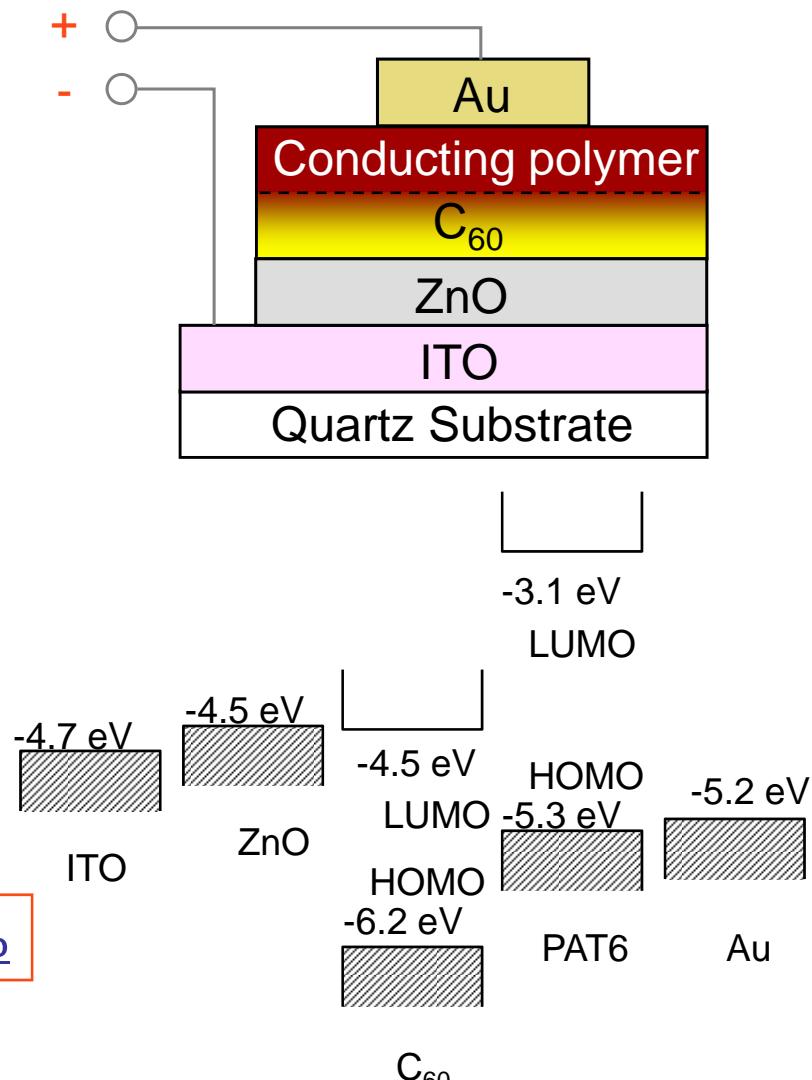


EQE: External Quantum Efficiency

Device Performance of Interpenetrating Junction Devices



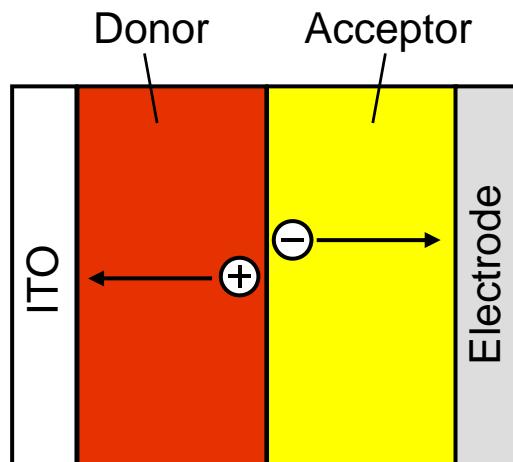
Energy conversion efficiency: 1.0%



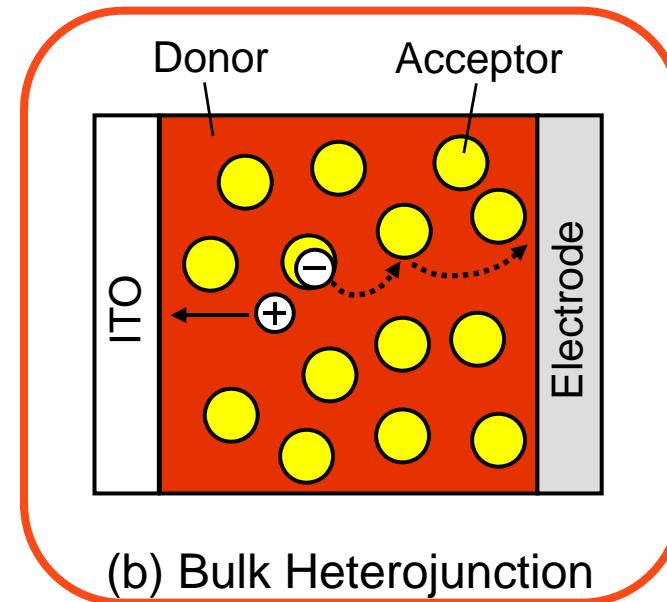
Ref.) T. Umeda, et al., Jpn. J. Appl. Phys. **42** (2003) L1475.

T. Shirakawa, et al., J. Phys. D: Appl. Phys. **37** (2004) 847.

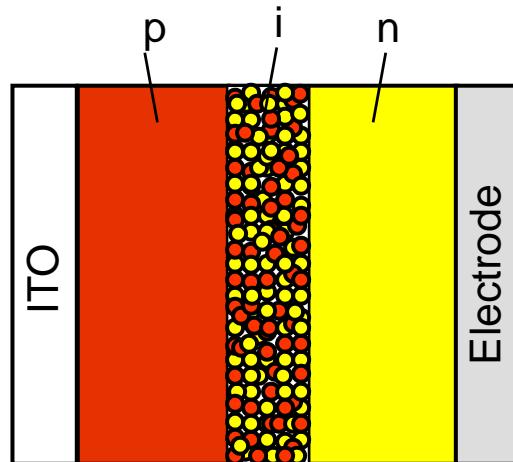
Fundamental Structures of D-A Type Photovoltaic Cells



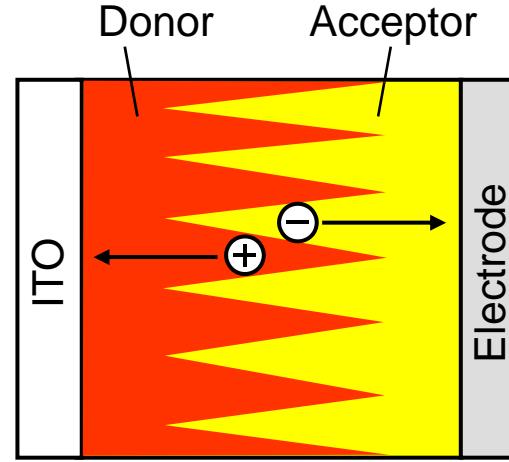
(a) Bi-layer type



(b) Bulk Heterojunction

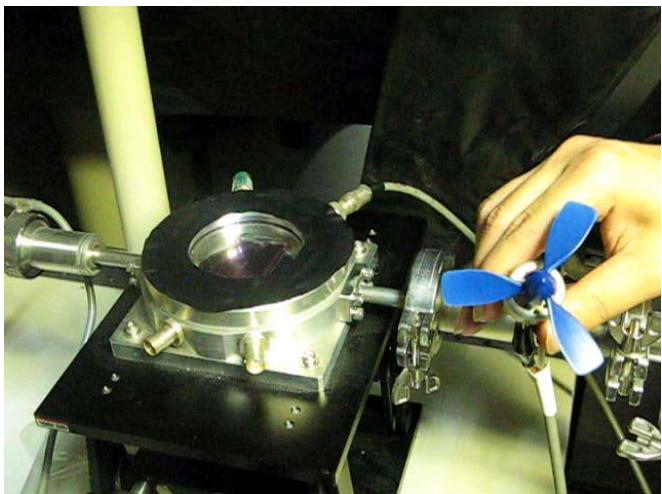
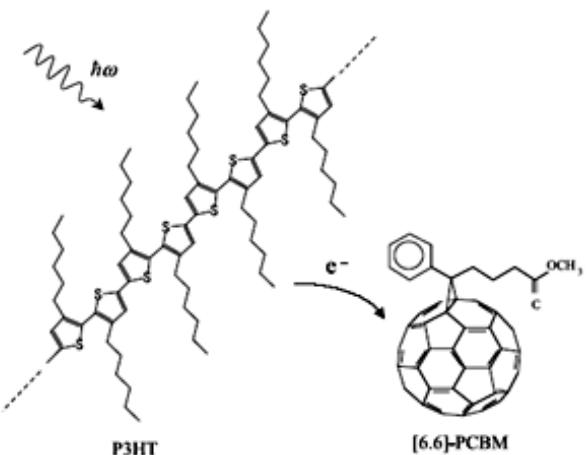
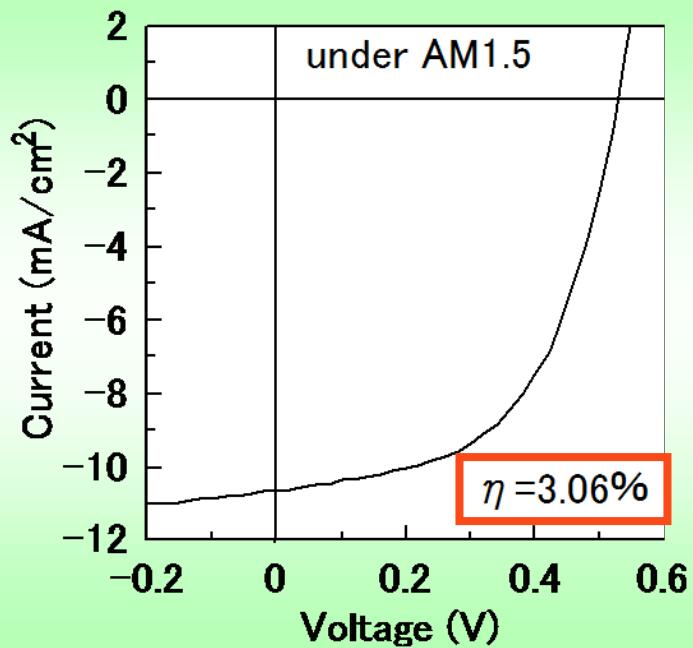
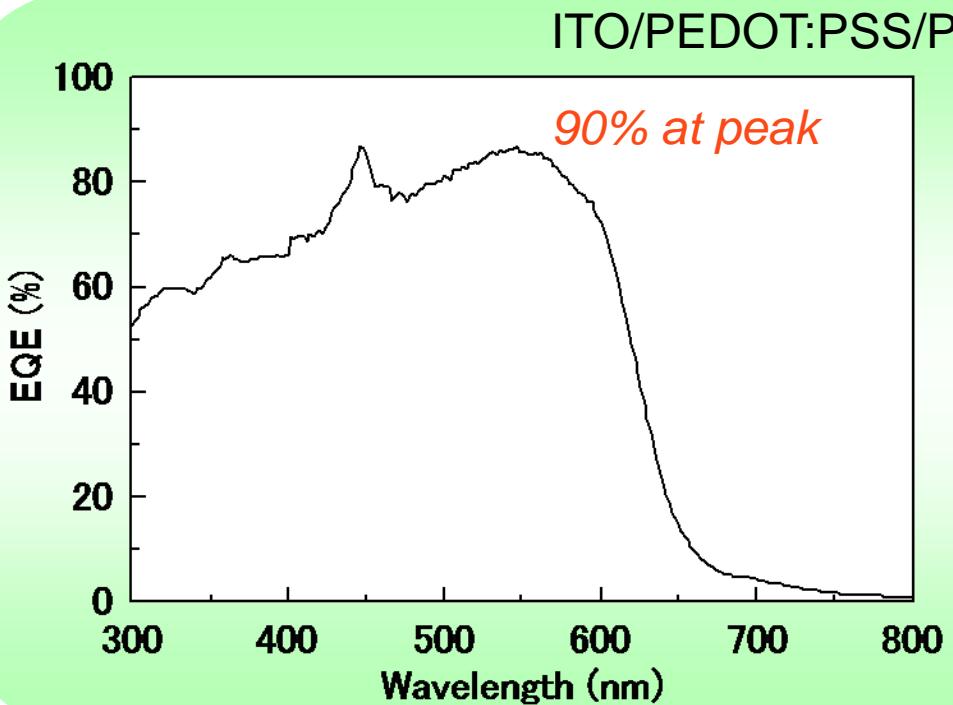


(c) p-i-n Junction Type



(d) Interpenetrating Junction

Device Performance of Bulk Heterojunction Devices



Previous Publications

Fundamental Study

Solvent Effects

Design of Inverse type Structure

Fundamental Interface Studies

Mixed Solvent Effects

ITO Surface Modification Effects

Co-evaporation Layer and Wide Range Sensitivity

Insertion of Oxide Semiconductor Layer

Film Fabrication by Spray Method

A. Fujii et al., Jpn. J. Appl. Phys.
43 (2004) 5573

A. Fujii et al., Jpn. J. Appl.
Phys. 43 (2004) 8312

T. Umeda et al., Jpn. J. Appl.
Phys. 42 (2003) L1475

T. Umeda et al., Jpn. J. Appl.
Phys. 44 (2005) 4155

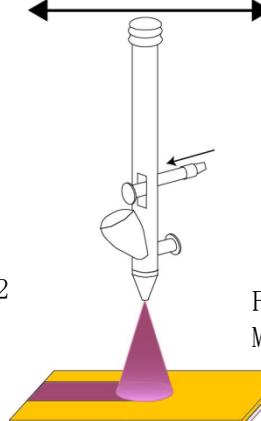
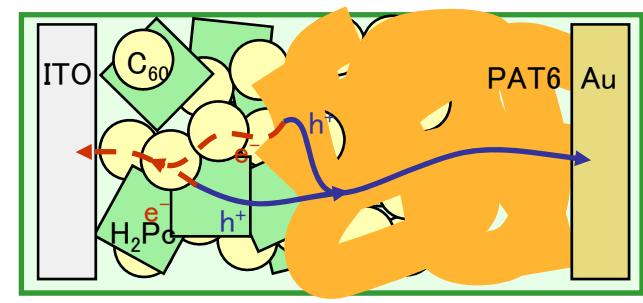
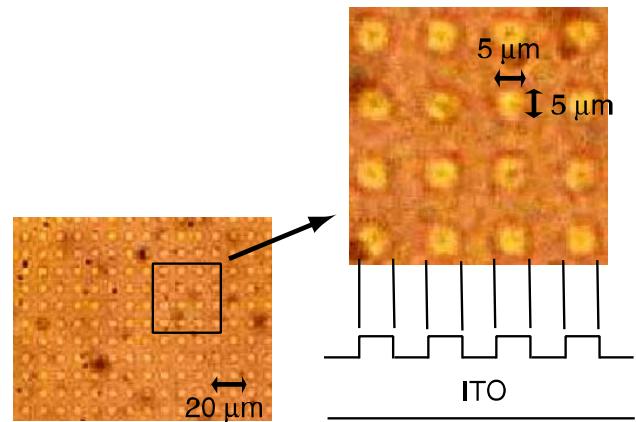
H. Mizaukami et al., J. Phys. D:
Appl. Phys. 39 (2006) 1521

Y. Hashimoto et al., Jpn. J.
Appl. Phys. 44 (2005) 1978

T. Umeda et al., Jpn. J. Appl.
Phys. 44 (2006) 538

T. Shirakawa et al., J.
Phys. D: Appl. Phys. 37
(2004) 847

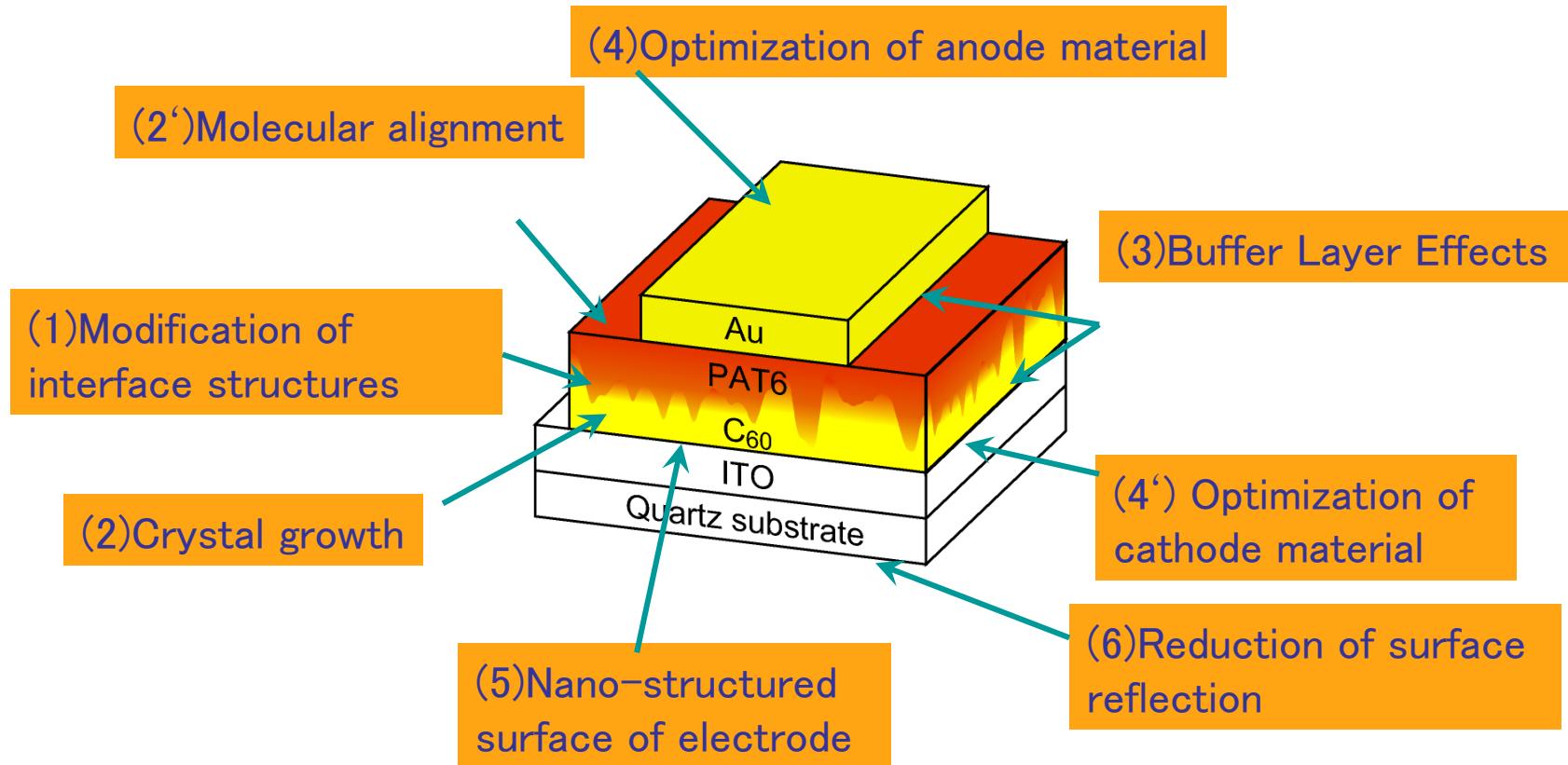
H. Noda et al., Jpn. J.
Appl. Phys. 45 (2006) 2792



Film Fabrication by Spray Method

Future Plans

We try to Investigate as follows for realizing high performance organic photovoltaic devices.



The detailed studies are now in progress.

Collaboration in our IDER unit

